

B55NF06-VB Datasheet

N-Channel 60-V (D-S) MOSFET

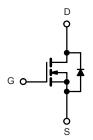
PRODUCT SUMMARY					
V_{DS}	60	V			
$R_{DS(on)} V_{GS} = 10 V$	11	mΩ			
$R_{DS(on)}$ $V_{GS} = 4.5 \text{ V}$	12	mΩ			
I _D	75	Α			
Configuration	Single				

FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET







N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Dunin Courset (T. = 475 °C)b	T _C = 25 °C	,	75		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	I _D	50 ^a		
Pulsed Drain Current		I _{DM}	200	Α	
Continuous Source Current (Diode Conduction)	I _S	50 ^a			
Avalanche Current		I _{AS}	50		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Manifestor Device Disable alian	T _C = 25 °C	D.	136	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	3 ^b , 8.3 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Mandana da Anakianta	t ≤ 10 sec	R_{thJA}	15	18	°C/W		
Maximum Junction-to-Ambient ^a	Steady State		40	50			
Maximum Junction-to-Case		R _{thJC}	0.85	1.1			

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s}$.

服务热线:400-655-8788

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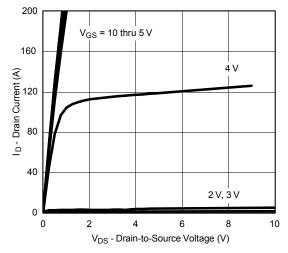
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static			L		<u> </u>		
Drain-Source Breakdown Voltage V		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V	
Gate Threshold Voltage	V _{GS(th)}	$V_{GS(th)}$ $V_{DS} = V_{GS}$, $I_D = 250 \mu A$			3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V	1		1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α	
		V _{GS} = 10 V, I _D = 20 A		0.011			
	_D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C	0.016			Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.020			
		V _{GS} = 4.5 V, I _D = 15 A		0.012		1	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic	•			•			
Input Capacitance	C _{iss}			4300			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470		pF	
Reverse Transfer Capacitance	C _{rss}			225		1	
Total Gate Charge ^c	Q_g			47			
Gate-Source Charge ^c	Q_{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_{D} = 50 A		10		nC	
Gate-Drain Charge ^c	Q _{gd}			12		1	
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN}$ = 10 V, R_g = 2.5 Ω		35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)		_			
Pulsed Current	I _{SM}				60	Α	
Diode Forward Voltage	V _{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t _{rr}	$I_F = 20 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$		45	100	ns	

- a. For design aid only; not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

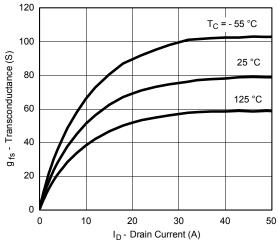
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



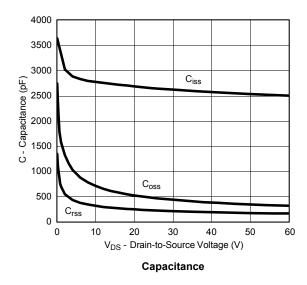
TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics

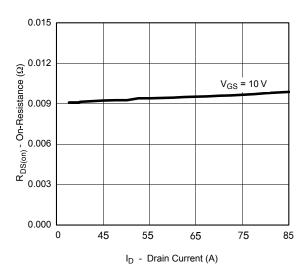


Transconductance

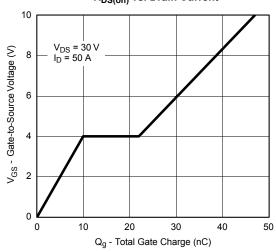


100 80 I_D - Drain Current (A) 60 40 T_C = 125 °C 20 25 °C - 55 °C 0 0 1 2 3 4 5 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



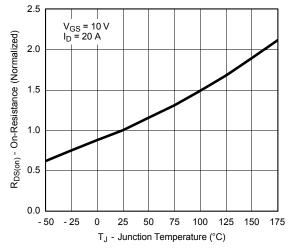
R_{DS(on)} vs. Drain Current



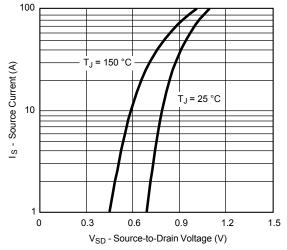
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



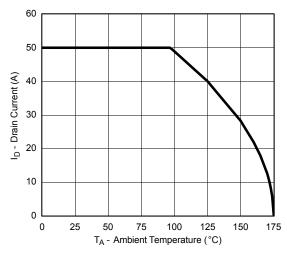
On-Resistance vs. Junction Temperature

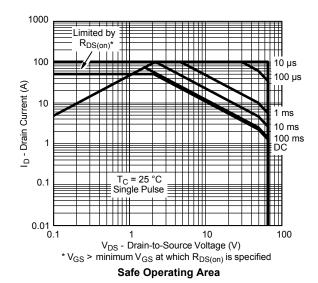


Source-Drain Diode Forward Voltage

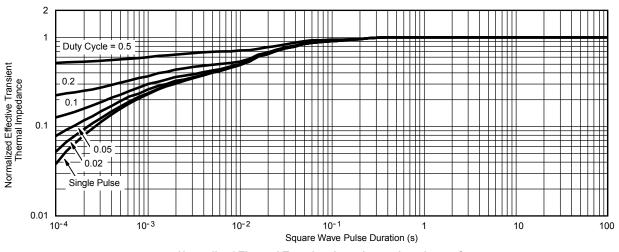


THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



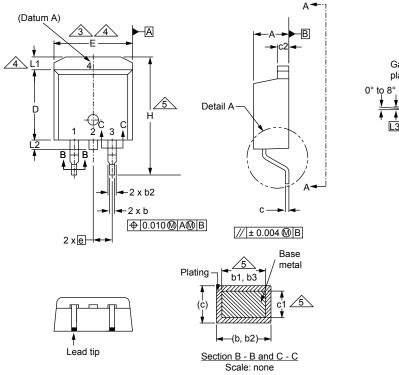
Normalized Thermal Transient Impedance, Junction-to-Case

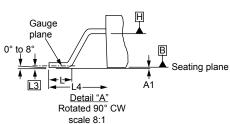
服务热线:400-655-8788

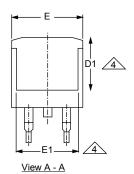
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TO-263AB (HIGH VOLTAGE)







	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
С	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

9.65

0.330

0.380

	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
D1	6.86	-	0.270	-	
Е	9.65	10.67	0.380	0.420	
E1	6.22	-	0.245	-	
е	2.54	BSC	0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	
L2	-	1.78	-	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

8.38 ECN: S-82110-Rev. A, 15-Sep-08

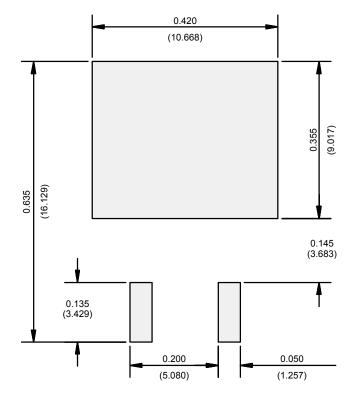
DWG: 5970

D

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
- 4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
- 5. Dimension b1 and c1 apply to base metal only.
- 6. Datum A and B to be determined at datum plane H.
- 7. Outline conforms to JEDEC outline to TO-263AB.



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)



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